

# DF3A6.8FUT1

Preferred Device

## Zener ESD Protection Diode

### Dual Common Anode Zeners for ESD Protection

These dual monolithic silicon zener diodes are designed for applications requiring transient overvoltage protection capability. They are intended for use in voltage and ESD sensitive equipment such as computers, printers, business machines, communication systems, medical equipment and other applications. Their dual junction common anode design protects two separate lines using only one package. These devices are ideal for situations where board space is at a premium.

#### Features

- Pb-Free Package is Available
- SC-70 Package Allows Two Separate Unidirectional Configurations
- Low Leakage < 1.0  $\mu$ A @ 5.0 V
- Breakdown Voltage: 6.4–7.2 V @ 5.0 mA
- ESD Protection Meeting: 16 kV Human Body Model  
30 kV Contact = IEC61000-4-2
- Peak Power: 24 W @ 1.0 ms (Unidirectional), per Figure 1
- Peak Power: 150 W @ 20  $\mu$ s (Unidirectional), per Figure 2

#### Mechanical Characteristics

- Void Free, Transfer-Molded, Thermosetting Plastic Case
- Corrosion Resistant Finish, Easily Solderable
- Package Designed for Optimal Automated Board Assembly
- Small Package Size for High Density Applications

#### MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Steady State Power Dissipation Derate above 25°C (Note 1)	$P_D$	200 1.6	mW mW/°C
Thermal Resistance Junction-to-Ambient	$R_{\theta JA}$	618	°C/W
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	- 55 to +150	°C
Peak Power Dissipation @ 1.0 ms (Note 2) @ $T_A = 25^\circ\text{C}$	$P_{PK}$	20	W
Peak Power Dissipation @ 20 $\mu$ s (Note 3) @ $T_A = 25^\circ\text{C}$	$P_{PK}$	150	W
ESD Discharge MIL STD 883C – Method 3015-6 IEC61000-4-2, Air Discharge IEC61000-4-2, Contact Discharge	$V_{PP}$	16 30 30	kV

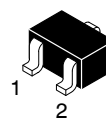
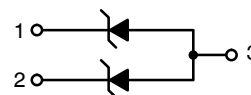
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Mounted on FR-5 Board = 1.0 X 0.75 X 0.062 in.
2. Non-repetitive pulse per Figure 1.
3. Non-repetitive pulse per Figure 2.



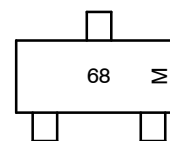
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SC-70/SOT-323  
CASE 419  
STYLE 4

#### MARKING DIAGRAM



68 = Specific Device Code  
M = Date Code

#### ORDERING INFORMATION

Device	Package	Shipping†
DF3A6.8FUT1	SC-70	3000/Tape & Reel
DF3A6.8FUT1G	SC-70 (Pb-Free)	3000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

Preferred devices are recommended choices for future use and best overall value.

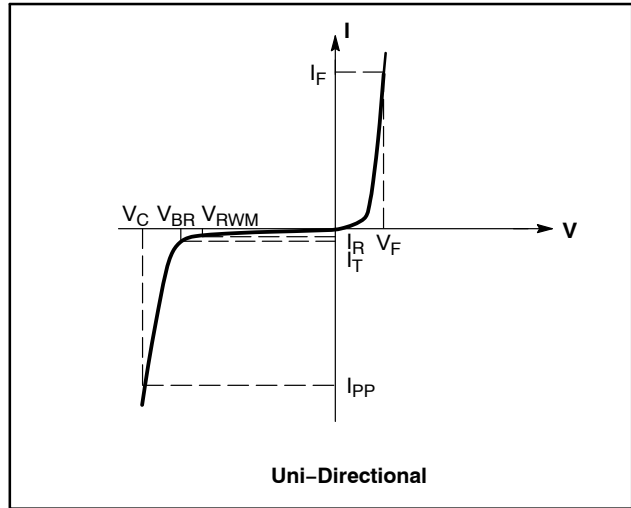
# DF3A6.8FUT1

## ELECTRICAL CHARACTERISTICS

( $T_A = 25^\circ\text{C}$  unless otherwise noted)

**UNIDIRECTIONAL** (Circuit tied to Pins 1 and 3 or 2 and 3)

Symbol	Parameter
$V_{RWM}$	Working Peak Reverse Voltage
$I_R$	Maximum Reverse Leakage Current @ $V_{RWM}$
$V_{BR}$	Breakdown Voltage @ $I_T$
$I_T$	Test Current
$I_F$	Forward Current
$V_F$	Forward Voltage @ $I_F$
$Z_{ZT}$	Maximum Zener Impedance @ $I_{ZT}$
$Z_{ZK}$	Maximum Zener Impedance @ $I_{ZK}$



## ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

**UNIDIRECTIONAL** (Circuit tied to Pins 1 and 3 or 2 and 3)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Forward Voltage	$V_F$	$I_F = 10 \text{ mA}$		0.8	0.9	V
Zener Voltage (Note 4)	$V_Z$	$I_{ZT} = 5 \text{ mA}$	6.4	6.8	7.2	V
Operating Resistance (Note 5)	$Z_{ZK}$	$I_{ZK} = 0.5 \text{ mA}$			200	$\Omega$
	$Z_{ZT}$	$I_{ZT} = 5 \text{ mA}$			50	$\Omega$
Reverse Current	$I_{R1}$	$V_{RWM} = 5 \text{ V}$			0.5	$\mu\text{A}$
Clamping Voltage	$V_C$	$I_{PP} = 2.0 \text{ A}$ (Figure 1)			9.6	V
		$I_{PP} = 9.37 \text{ A}$ (Figure 2)			16	V
ESD Protection Human Body Model (HBM) Contact – IEC61000-4-2 Air Discharge					16	kV
					30	
					30	

4.  $V_Z$  measured at pulse test current  $I_{ZT}$  at an ambient temperature of  $25^\circ\text{C}$ .

5.  $Z_{ZT}$  and  $Z_{ZK}$  is measured by dividing the AC voltage drop across the device by the AC current supplied. AC frequency = 1.0 kHz.

TYPICAL CHARACTERISTICS

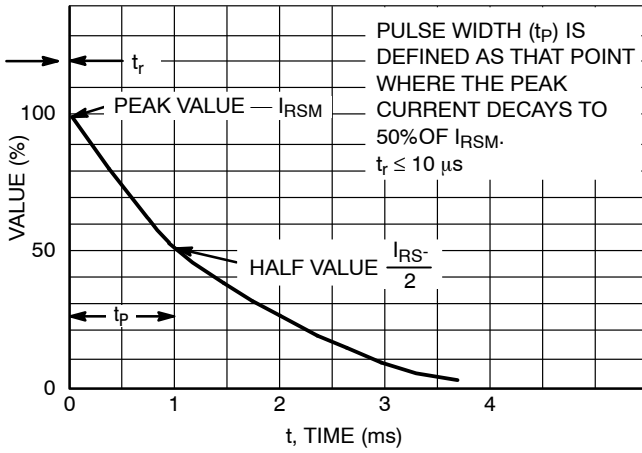


Figure 1. 10 × 1000 μs Pulse Waveform

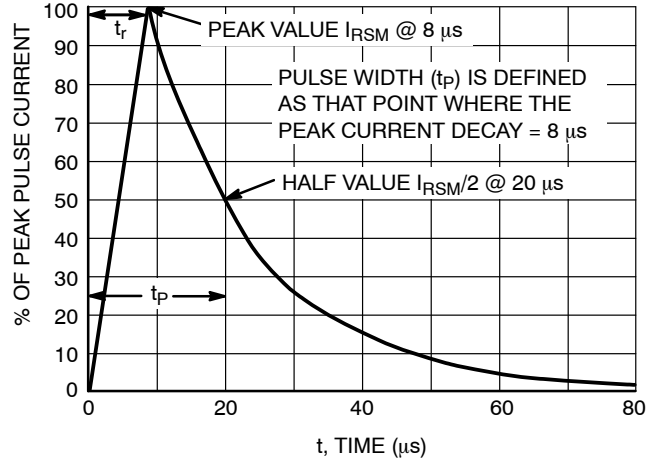


Figure 2. 8 × 20 μs Pulse Waveform

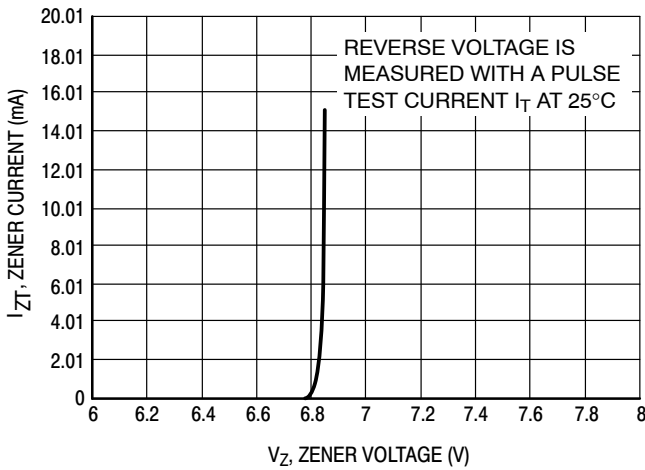


Figure 3. Zener Voltage vs. Zener Current

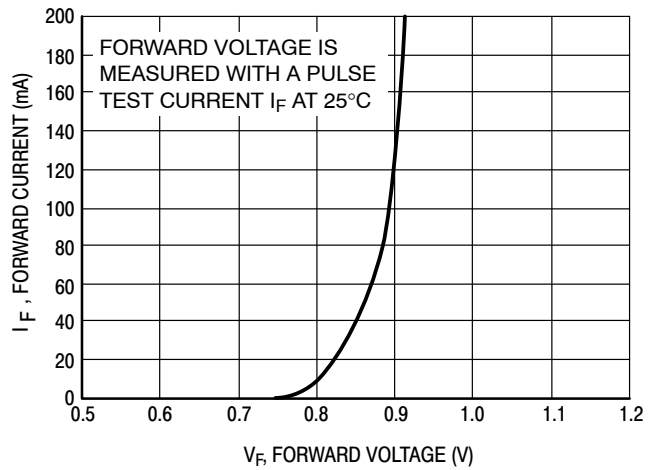


Figure 4. Forward Voltage vs. Forward Current

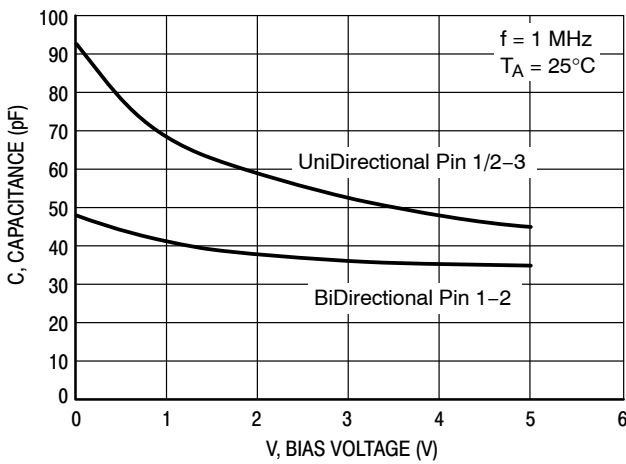


Figure 5. Capacitance vs. Bias Voltage

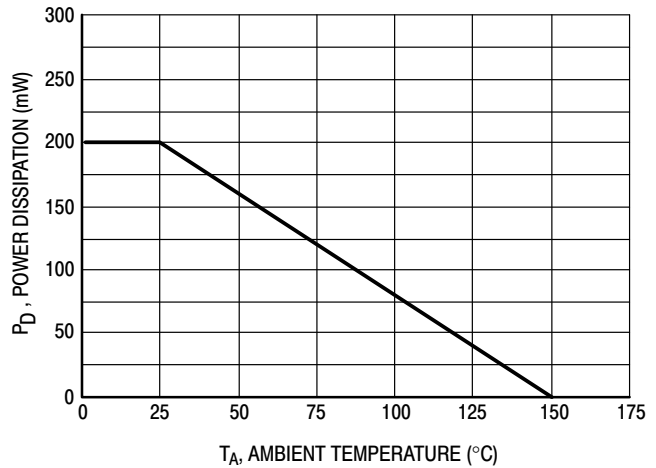


Figure 6. Steady State Power Derating Curve

# MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS



SCALE 4:1

## SC-70 (SOT-323) CASE 419 ISSUE R

DATE 11 OCT 2022



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH

DIM	MILLIMETERS			INCHES		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	0.80	0.90	1.00	0.032	0.035	0.040
A1	0.00	0.05	0.10	0.000	0.002	0.004
A2	0.70 REF			0.028 BSC		
b	0.30	0.35	0.40	0.012	0.014	0.016
c	0.10	0.18	0.25	0.004	0.007	0.010
D	1.80	2.00	2.20	0.071	0.080	0.087
E	1.15	1.24	1.35	0.045	0.049	0.053
e	1.20	1.30	1.40	0.047	0.051	0.055
e1	0.65 BSC			0.026 BSC		
L	0.20	0.38	0.56	0.008	0.015	0.022
H <sub>E</sub>	2.00	2.10	2.40	0.079	0.083	0.095

### GENERIC MARKING DIAGRAM



- XX = Specific Device Code
- M = Date Code
- = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.



\* For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERM/D.

### SOLDERING FOOTPRINT

- |   |   |   |  |   |   |
|---|---|---|--|---|---|
| STYLE 1:<br>CANCELLED                                 | STYLE 2:<br>PIN 1. ANODE<br>2. N.C.<br>3. CATHODE     | STYLE 3:<br>PIN 1. BASE<br>2. EMITTER<br>3. COLLECTOR | STYLE 4:<br>PIN 1. CATHODE<br>2. CATHODE<br>3. ANODE       | STYLE 5:<br>PIN 1. ANODE<br>2. ANODE<br>3. CATHODE          |   |
| STYLE 6:<br>PIN 1. EMITTER<br>2. BASE<br>3. COLLECTOR | STYLE 7:<br>PIN 1. BASE<br>2. EMITTER<br>3. COLLECTOR | STYLE 8:<br>PIN 1. GATE<br>2. SOURCE<br>3. DRAIN      | STYLE 9:<br>PIN 1. ANODE<br>2. CATHODE<br>3. CATHODE-ANODE | STYLE 10:<br>PIN 1. CATHODE<br>2. ANODE<br>3. ANODE-CATHODE | STYLE 11:<br>PIN 1. CATHODE<br>2. CATHODE<br>3. CATHODE |

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<b>DESCRIPTION:</b>	<b>SC-70 (SOT-323)</b>	<b>PAGE 1 OF 1</b>

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